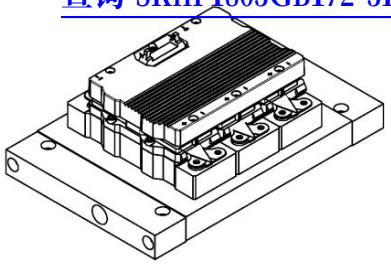
SKiiP 1803GB172-3DW



SKiiP® 3

2-pack-integrated intelligent Power System

Power section

SKiiP 1803GB172-3DW

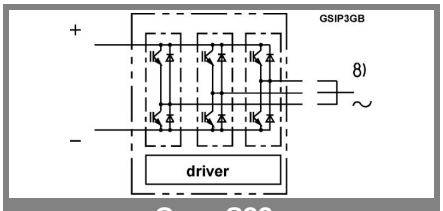
Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated teperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532

1) with assembly of suitable MKP capacitor per terminal

8) AC connection busbars must be connected by the user; copper busbars available on request



Case S33

Absolute Maximum Ratings		T_s = 25°C unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1700	V
V_{CC} 1)	Operating DC link voltage	1200	V
V_{GES}		± 20	V
I_C	T_s = 25 (70) °C	1800 (1350)	A
Inverse diode			
I_F = - I_C	T_s = 25 (70) °C	1400 (1050)	A
I_{FSM}	T_j = 150 °C, t_p = 10 ms; sin	10200	A
I²t (Diode)	Diode, T_j = 150 °C, 10 ms	520	kA²s
T_j, (T_{stg})		- 40 ... + 150 (125)	°C
V_{isol}	rms, AC, 1 min, main terminals to heat sink	4000	V
$I_{AC\text{-}terminal}$	per AC terminal, rms, T_s = 70 °C, $T_{terminal}$ <115 °C	400	A

Characteristics		T_s = 25°C unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
V_{CEsat}	I_C = 900 A, T_j = 25 (125) °C; measured at terminal		1,9 (2,2)	2,4	V
V_{CEO}	T_j = 25 (125) °C; at terminal		1 (0,9)	1,2 (1,1)	V
r_{CE}	T_j = 25 (125) °C; at terminal		1 (1,4)	1,3 (1,7)	mΩ
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}, T_j = 25 (125) °C		3,6 (216)		mA
E_{on} + E_{off}	I_C = 900 A, V_{CC} = 900 V		585		mJ
	T_j = 125 °C, V_{CC} = 1200 V		863		mJ
$R_{CC+EE'}$	terminal chip, T_j = 25 °C		0,17		mΩ
L_{CE}	top, bottom		4		nH
C_{CHC}	per phase, AC-side		3		nF
Inverse diode					
V_F = V_{EC}	I_F = 900 A, T_j = 25 (125) °C measured at terminal		2 (1,8)	2,15	V
V_{TO}	T_j = 25 (125) °C		1,1 (0,8)	1,2 (0,9)	V
r_T	T_j = 25 (125) °C		1 (1,1)	1,1 (1,2)	mΩ
E_{rr}	I_C = 900 A, V_{CC} = 900 V		108		mJ
	T_j = 125 °C, V_{CC} = 1200 V		128		mJ
Mechanical data					
M_{dc}	DC terminals, SI Units	6		8	Nm
M_{ac}	AC terminals, SI Units	13		15	Nm
w	SKiiP® 3 System w/o heat sink		2,4		kg
w	heat sink		5,2		kg

Thermal characteristics (NWK 40; 8l/min; 50%glyc); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc.IEC 60747-15)

$R_{th(j\text{-}s)I}$	per IGBT						0,017	K/W
$R_{th(j\text{-}s)D}$	per diode						0,033	K/W
Z_{th}	R_i (mK/W) (max. values)				tau_i(s)			
	1	2	3	4	1	2	3	4
$Z_{th(j\text{-}r)I}$	1,4	6,8	7,8	0	69	0,35	0,02	1
$Z_{th(j\text{-}r)D}$	2,6	4	17,7	17,7	50	5	0,25	0,04
$Z_{th(r\text{-}a)}$	4,6	4,7	1,1	0,6	48	15	2,8	0,4

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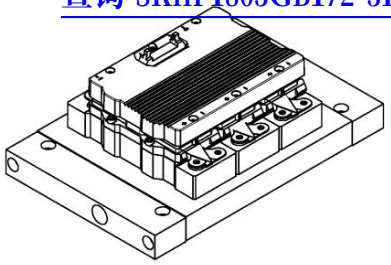

SKiiP® 3

2-pack-integrated intelligent Power System

2-pack
integrated gate driver
SKiiP 1803GB172-3DW

Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute Maximum Ratings T_a = 25°C unless otherwise specified

Symbol	Conditions	Values	Units
V_{S2}	unstabilized 24 V power supply	30	V
V_i	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/µs
V_{isolIO}	input / output (AC, rms, 2s)	4000	V
V_{isolPD}	partial discharge extinction voltage, rms, Q_{PD} ≤10 pC;	1500	V
V_{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V
f_{sw}	switching frequency	9	kHz
f_{out}	output frequency for $I_{peak(1)}=I_C$	9	kHz
T_{op} (T_{stg})	operating / storage temperature	- 40 ... + 85	°C

Characteristics (T_a = 25°C)

Symbol	Conditions	min.	typ.	max.	Units
V_{S2}	supply voltage non stabilized	13	24	30	V
I_{S2}	V_{S2} = 24 V		380+34*f/kHz+0,00015*(I_{AC}/A)^2		mA
V_{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R_{IN}	input resistance		10		kΩ
C_{IN}	input capacitance		1		nF
$t_{d(on)IO}$	input-output turn-on propagation time		1,3		µs
$t_{d(off)IO}$	input-output turn-off propagation time		1,3		µs
$t_{pERRRESET}$	error memory reset time		9		µs
t_{TD}	top / bottom switch interlock time		3,3		µs
$I_{analogOUT}$	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1500		A
I_{s1out}	max. load current			50	mA
I_{TRIPSC}	over current trip level (I_{analog} OUT = 10 V)		1875		A
T_{tp}	over temperature protection	110		120	°C
U_{DCTRIP}	U_{DC}-protection ($U_{analog\ OUT}$ = 9 V); (option for GB types)		not implemented		V

For electrical and thermal design support please use SEMISEL.
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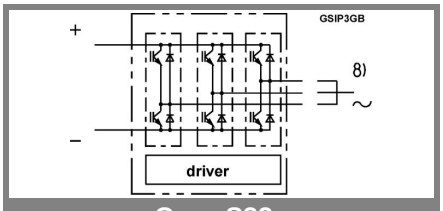

Case S33

